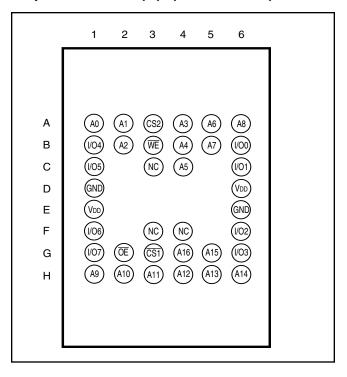
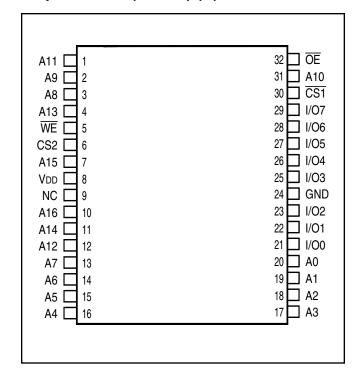


PIN CONFIGURATION 36-pin mini BGA (B) (6mm x 8mm)



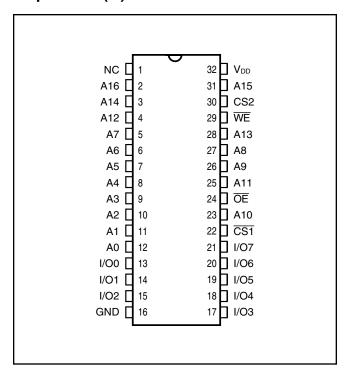
32-pin TSOP (TYPE I) (T), 32-pin sTSOP (TYPE I) (H)



PIN DESCRIPTIONS

A0-A16	Address Inputs
CS1	Chip Enable 1 Input
CS2	Chip Enable 2 Input
ŌĒ	Output Enable Input
WE	Write Enable Input
I/O0-I/O7	Input/Output
NC	No Connection
VDD	Power
GND	Ground

32-pin SOP (Q)





ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Parameter	Value	Unit	
VTERM	Terminal Voltage with Respect to GND	-0.2 to VDD+0.3	V	
V _{DD}	VDD Related to GND	-0.2 to +3.8	V	
Тѕтс	Storage Temperature	-65 to +150	°C	
Рт	Power Dissipation	1.0	W	

Note:

OPERATING RANGE (VDD)

Range	Ambient Temperature	IS62WV1288ALL	IS62/65WV1288BLL
Commercial	0°C to +70°C	1.65V - 2.2V	2.5V - 3.6V
Industrial/A1	−40°C to +85°C	1.65V - 2.2V	2.5V - 3.6V
Automotive	-40°C to +125°C		2.5V - 3.6V

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions	V _{DD}	Min.	Max.	Unit
Vон	Output HIGH Voltage	Iон = -0.1 mA	1.65-2.2V	1.4	_	V
	,	IOH = -1 mA	2.5-3.6V	2.2	_	V
Vol	Output LOW Voltage	IoL = 0.1 mA	1.65-2.2V	_	0.2	V
	-	IoL = 2.1 mA	2.5-3.6V	_	0.4	V
$V_{IH}^{(2)}$	Input HIGH Voltage		1.65-2.2V	1.4	V _{DD} + 0.2	V
			2.5-3.6V	2.2	$V_{DD} + 0.3$	V
VIL ⁽¹⁾	Input LOW Voltage		1.65-2.2V	-0.2	0.4	V
			2.5-3.6V	-0.2	0.6	V
lu	Input Leakage	$GND \leq V_{IN} \leq V_{DD}$		-1	1	μA
ILO	Output Leakage	$GND \leq Vout \leq Vpd$, C	Outputs Disabled	-1	1	μΑ

Notes:

- 1. Undershoot: -1.0V for pulse width less than 10 ns. Not 100% tested.
- 2. Overshoot: VDD + 1.0V for pulse width less than 10 ns. Not 100% tested.

TRUTH TABLE

Mode	WE	CS1	CS2	ŌĒ	I/O Operation	VDD Current
Not Selected	Х	Н	Х	Х	High-Z	ISB1, ISB2
(Power-down)	Χ	Χ	L	Χ	High-Z	ISB1, ISB2
Output Disabled	Н	L	Н	Н	High-Z	Icc
Read	Н	L	Н	L	D ouт	Icc
Write	L	L	Н	Χ	Din	Icc

Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a
stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational
sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.



CAPACITANCE(1)

Symbol	Parameter	Conditions	Max.	Unit	
CIN	Input Capacitance	$V_{IN} = 0V$	8	pF	
Соит	Input/Output Capacitance	Vout = 0V	10	pF	

Note:

ACTEST CONDITIONS

Parameter	62WV1288ALL	62/65WV1288BLL
	(Unit)	(Unit)
Input Pulse Level	0.4V to V _{DD} -0.2V	0.4V to VDD-0.3V
Input Rise and Fall Times	5 ns	5ns
Input and Output Timing and Reference Level	Vref	VREF
Output Load	See Figures 1 and 2	See Figures 1 and 2

	1.65V - 2.2V	2.5V - 3.6V
R1(Ω)	3070	3070
R2(Ω)	3150	3150
VREF	0.9V	1.5V
Vтм	1.8V	2.8V

ACTEST LOADS

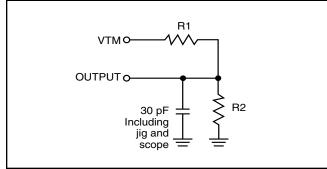
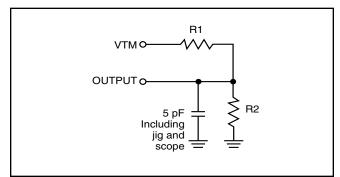


Figure 1 Figure 2



^{1.} Tested initially and after any design or process changes that may affect these parameters.



POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

1.65V - 2.2V

Symbol	Parameter	Test Conditions		Max. 70 ns	Unit
Icc	V _{DD} Dynamic Operating Supply Current	VDD = Max., IOUT = 0 mA, f = fMAX	Com. Ind.	8 8	mA
	Сарру Санон	1001 – 0 111/1, 1 – 111/100	typ. ⁽²⁾	5	
Icc1	Operating Supply	V _{DD} = Max.,	Com.	5	mA
	Current	IOUT = 0 mA, f = 0	Ind.	5	
Is _B 1	TTL Standby Current	V _{DD} = Max.,	Com.	0.8	mA
	(TTL Inputs)		Ind.	0.8	
IsB2	CMOS Standby	$V_{DD} = Max.,$	Com.	10	μΑ
	Current (CMOS Inputs)	$\overline{\text{CS1}} \ge V_{\text{DD}} - 0.2V$,	Ind.	10	
		$\begin{split} & \text{CS2} \leq 0.2\text{V}, \\ & \text{V}_{\text{IN}} \geq \text{V}_{\text{DD}} - 0.2\text{V}, \text{or} \\ & \text{V}_{\text{IN}} \leq 0.2\text{V}, \text{f} = 0 \end{split}$	typ. ⁽²⁾	5	

Note:

POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

2.5V - 3.6V

Symbol	Parameter	Test Conditions		Max. 45ns	Max. 55 ns	Unit
Icc	VDD Dynamic Operating	$V_{DD} = Max.,$	Com.	17	15	mA
	Supply Current	IOUT = 0 mA, f = fMAX	Ind./A1	17	15	
			A3		35	
			typ. ⁽²⁾	12	10	
Icc1	Operating Supply	VDD = Max.,	Com.	5	5	mA
	Current	IOUT = 0 mA, f = 0	Ind./A1	5	5	
			A3		7	
Is _B 1	TTL Standby Current	VDD = Max.,	Com.	0.8	0.8	mA
	(TTL Inputs)	VIN = VIH or VIL	Ind./A1	0.8	0.8	
		$\overline{\text{CS1}} = \text{V}_{\text{IH}}$, $\text{CS2} = \text{V}_{\text{IL}}$, $\text{f} = 1 \text{ MHz}$	A3		3	
IsB2	CMOS Standby	V _{DD} = Max.,	Com.	10	10	μA
	Current (CMOS Inputs)	$\overline{\text{CS1}} \ge \text{V}_{\text{DD}} - 0.2\text{V},$	Ind./A1	10	10	'
	(CS2 ≤ 0.2V,	A3	-	75	
		$V_{IN} \ge V_{DD} - 0.2V, \text{ or } $ $V_{IN} \le 0.2V, f = 0$	typ. ⁽²⁾	5	5	

Note:

^{1.} At f = fmax, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.

^{2.} Typical values are measured at VDD=1.8V, TA=25°C. Not 100% tested.

^{1.} At $f = f_{MAX}$, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.

^{2.} Typical values are measured at VDD=3.0V, TA=25°C. Not 100% tested.



READ CYCLE SWITCHING CHARACTERISTICS⁽¹⁾ (Over Operating Range)

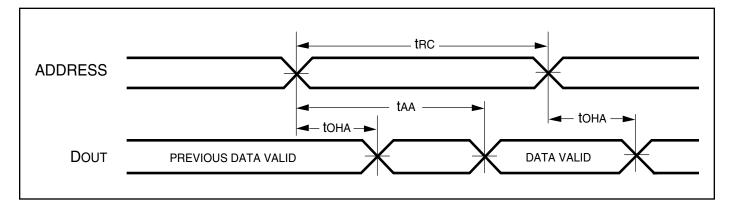
		45	ns	55	ns	70	ns	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
trc	Read Cycle Time	45	_	55	_	70		ns
taa	Address Access Time	_	45	_	55	_	70	ns
tона	Output Hold Time	10	_	10	_	10	_	ns
tacs1/tacs2	CS1/CS2 Access Time	_	45	_	55	_	70	ns
tdoe	OE Access Time	_	20	_	25	_	35	ns
thzoe(2)	OE to High-Z Output	0	15	0	20	0	25	ns
tlzoe ⁽²⁾	OE to Low-Z Output	5	_	5	_	5		ns
thzcs1/thzcs2(2)	CS1/CS2 to High-Z Output	0	15	0	20	0	25	ns
tLZCS1/tLZCS2 ⁽²⁾	CS1/CS2 to Low-Z Output	5	_	10	_	10		ns

Notes:

- 1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 0.9V/1.5V, input pulse levels of 0.4 to VDD-0.2V/VDD-0.3V and output loading specified in Figure 1.
- 2. Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.

AC WAVEFORMS

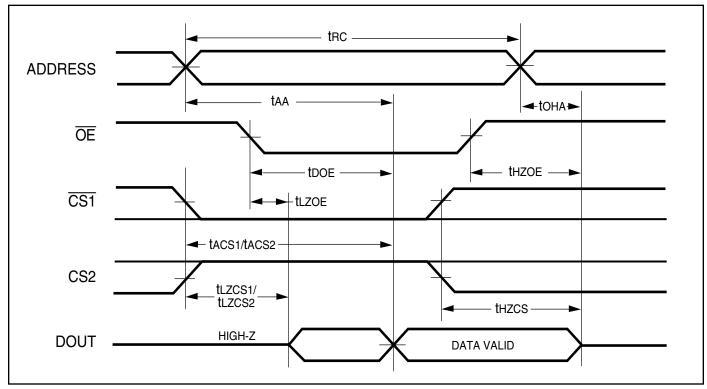
READ CYCLE NO. 1^(1,2) (Address Controlled) ($\overline{CS1} = \overline{OE} = VIL, CS2 = \overline{WE} = VIH)$





AC WAVEFORMS

READ CYCLE NO. 2^(1,3) ($\overline{CS1}$, CS2, \overline{OE} Controlled)



Notes:

- 1. WE is HIGH for a Read Cycle.
- 2. The device is continuously selected. \overline{OE} , $\overline{CS1}$ = V_IL. CS2= \overline{WE} =V_IH.
- 3. Address is valid prior to or coincident with $\overline{\text{CS1}}$ LOW and CS2 HIGH transition.



WRITE CYCLE SWITCHING CHARACTERISTICS(1,2) (Over Operating Range)

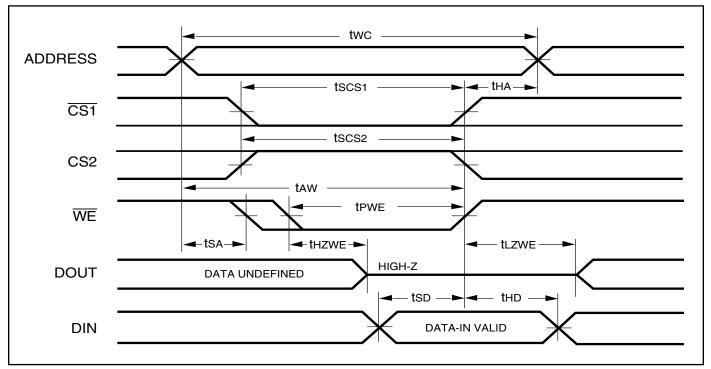
		45	ns	55	ns	70	ns	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
twc	Write Cycle Time	45	_	55	_	70	_	ns
tscs1/tscs2	CS1/CS2 to Write End	35	_	45	_	60	_	ns
taw	Address Setup Time to Write End	35	_	45	_	60	_	ns
tha	Address Hold from Write End	0	_	0	_	0	_	ns
t sa	Address Setup Time	0	_	0	_	0	_	ns
t PWE	WE Pulse Width	35	_	40	_	50	_	ns
tsd	Data Setup to Write End	20	_	25	_	30	_	ns
thd	Data Hold from Write End	0	_	0	_	0	_	ns
thzwE ⁽³⁾	WE LOW to High-Z Output	_	20	_	20	_	20	ns
tLZWE ⁽³⁾	WE HIGH to Low-Z Output	5	_	5	_	5	_	ns

Notes:

- 1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 0.9V/1.5V, input pulse levels of 0.4V to VDD-0.2V/VDD-0.3V and output loading specified in Figure 1.
- 2. The internal write time is defined by the overlap of $\overline{\text{CS1}}$ LOW, CS2 HIGH, and $\overline{\text{WE}}$ LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.
- 3. Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.

AC WAVEFORMS

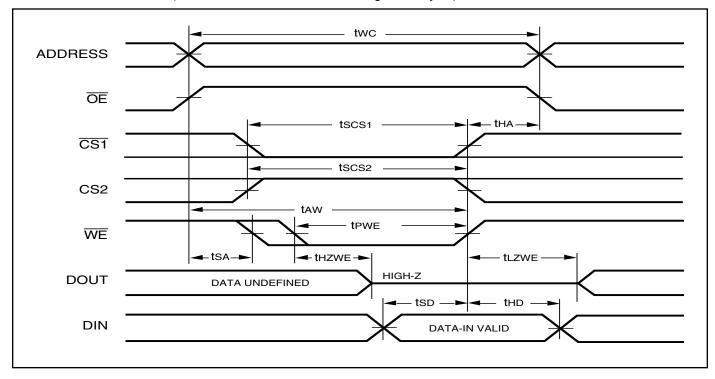
WRITE CYCLE NO. 1 (CS1/CS2 Controlled, OE = HIGH or LOW)



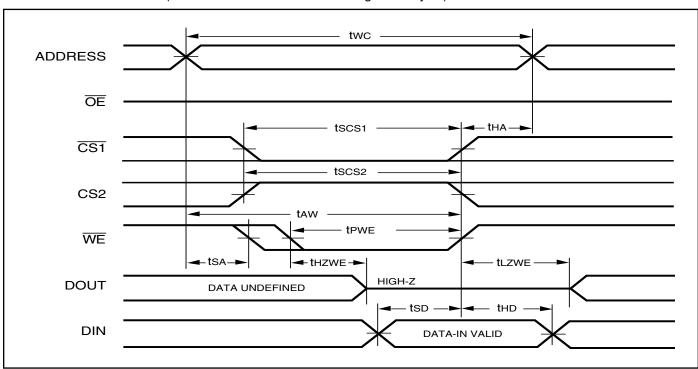


AC WAVEFORMS

WRITE CYCLE NO. 2 (WE Controlled: OE is HIGH During Write Cycle)



WRITE CYCLE NO. 3 (WE Controlled: OE is LOW During Write Cycle)

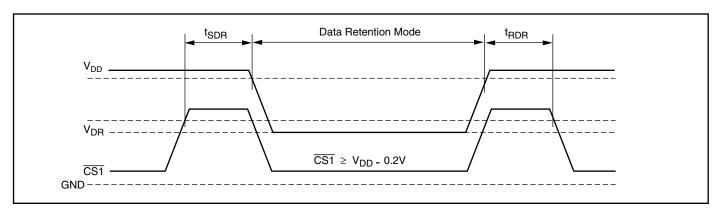




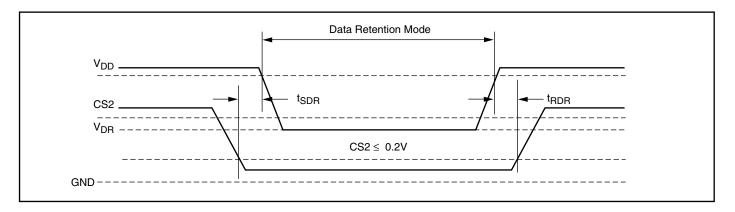
DATA RETENTION SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition		Min.	Max.	Unit
V DR	V _{DD} for Data Retention	See Data Retention Waveform		1.2	3.6	V
IDR	Data Retention Current	$V_{DD} = 1.2V, \overline{CS1} \ge V_{DD} - 0.2V$	Com.		5	μΑ
			Ind./A1	_	10	-
			A3	_	75	
tsdr	Data Retention Setup Time	See Data Retention Waveform		0	_	ns
trdr	Recovery Time	See Data Retention Waveform		trc	_	ns

DATA RETENTION WAVEFORM (CS1 Controlled)



DATA RETENTION WAVEFORM (CS2 Controlled)





ORDERING INFORMATION

IS62WV1288ALL (1.65V - 2.2V)

Industrial Range: -40°C to +85°C

Speed (ns)	Order Part No.	Package
70	IS62WV1288ALL-70BI	mini BGA (6mm x 8mm)
	IS62WV1288ALL-70HI	sTSOP, TYPE I

IS62WV1288BLL (2.5V-3.6V)

Industrial Range: -40°C to +85°C

Speed (ns)	Order Part No.	Package
45	IS62WV1288BLL-45TI	TSOP, TYPE I
	IS62WV1288BLL-45BI	mini BGA (6mm x 8mm)
	IS62WV1288BLL-45HI IS62WV1288BLL-45HLI	sTSOP, TYPE I sTSOP, TYPE I, Lead-free
	IS62WV1288BLL-45QI	SOP
55	IS62WV1288BLL-55TI IS62WV1288BLL-55TLI	TSOP, TYPE I TSOP, TYPE I, Lead-free
	IS62WV1288BLL-55BI	mini BGA (6mm x 8mm)
	IS62WV1288BLL-55HI IS62WV1288BLL-55HLI	sTSOP, TYPE I sTSOP, TYPE I, Lead-free
	IS62WV1288BLL-55QI IS62WV1288BLL-55QLI	SOP SOP, Lead-free

IS65WV1288BLL (2.5V-3.6V)

A1 Range: -40°C to +85°C

Speed (ns)	Order Part No.	Package
55	IS65WV1288BLL-55HLA1	sTSOP, TYPE I, Lead-free
	IS65WV1288BLL-55TLA1	TSOP, TYPE I, Lead-free

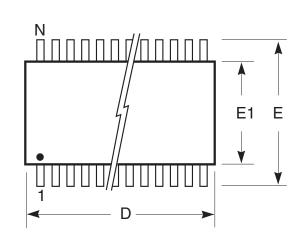
A3 Range: -40°C to +125°C

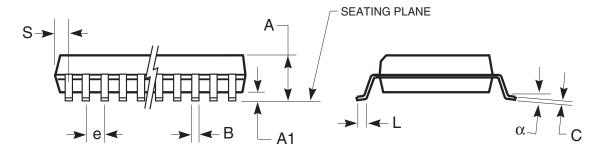
Speed (ns)	Order Part No.	Package
55	IS65WV1288BLL-55HLA3	sTSOP, TYPE I, Lead-free



450-mil Plastic SOP

Package Code: Q (32-pin)





	MILLIMETERS			INC	HES
Symbol	Min.	Max.		Min.	Max.
No. Leads			32		
A	_	3.00		_	0.118
A1	0.10	_		0.004	_
В	0.36	0.51		0.014	0.020
С	0.15	0.30		0.006	0.012
D	20.14	20.75		0.793	0.817
Е	13.87	14.38		0.546	0.566
E1	11.18	11.43		0.440	0.450
е	1.27 BSC			0.050	BSC
L	0.58	0.99		0.023	0.039
α	0°	10°		0°	10°
S	_	0.86		_	0.034

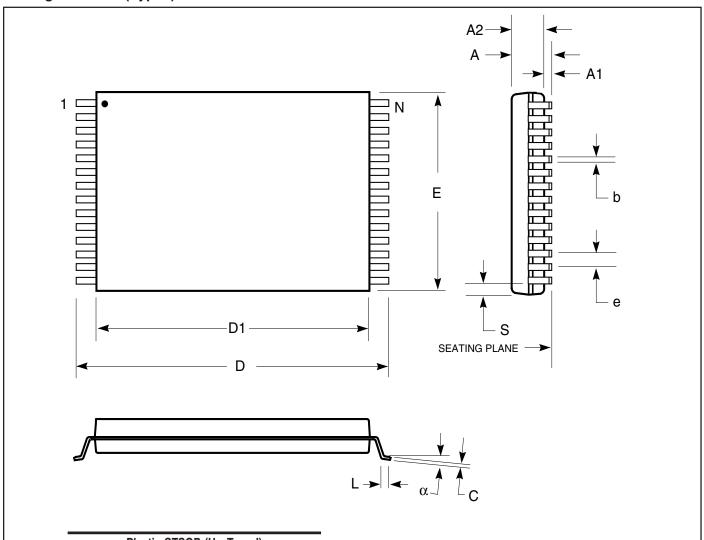
Notes:

- 1. Controlling dimension: inches, unless otherwise specified.
- 2. BSC = Basic lead spacing between centers.
- 3. Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.
- Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.

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Plastic STSOP - 32 pins Package Code: H (Type I)



Plastic STSOP (H - Type I)							
	Millim	eters	In	ches			
Symbol	Min Max		Min	Max			
Ref. Std.							
N			32				
Α	_	1.25	_	0.049			
A1	0.05	_	0.002	_			
A2	0.95	1.05	0.037	0.041			
b	0.17	0.23	0.007	0.009			
С	0.14	0.16	0.0055	0.0063			
D	13.20	13.60	0.520	0.535			
D1	11.70	11.90	0.461	0.469			
Е	7.90	8.10	0.311	0.319			
е	0.50 BSC		0.02	20 BSC			
L	0.30	0.70	0.012	0.028			
S	0.28 Typ.		0.0	11 Typ.			
α	0°	5°	0°	5°			

Notes:

- Controlling dimension: millimeters, unless otherwise specified.
- 2. BSC = Basic lead spacing between centers.
- Dimensions D1 and E do not include mold flash protrusions and should be measured from the bottom of the package.
- 4. Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.

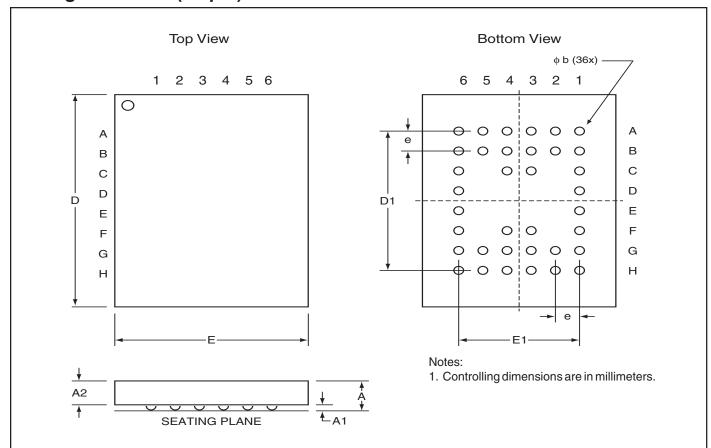
Integrated Silicon Solution, Inc.

PK13197H32 Rev.B 04/21/03



Mini Ball Grid Array

Package Code: B (36-pin)



mBGA - 6mm x 8mm

MILLIMETERS			INCHES			
Sym.	Min. Typ. Max.			Min. Typ. Max.		
N0. Leads		36		36		
Α	_	_	1.20	— — 0.047		
A1	0.24	_	0.30	0.009 — 0.012		
A2	0.60	_	_	0.024 — —		
D	7.90	8.00	8.10	0.311 0.315 0.319		
D1	5	.25BS	2	0.207BSC		
E	5.90	6.00	6.10	0.232 0.236 0.240		
E1	3.75BSC		C	0.148BSC		
е	0	.75BS	C	0.030BSC		
b	0.30	0.35	0.40	0.012 0.014 0.016		

mBGA - 8mm x 10mm

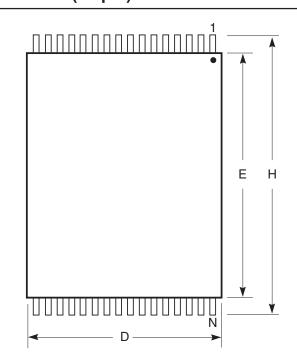
MILLIMETER			INCHES			
Sym.	Min. Typ. Max.		Max.	Min. Typ. Max.		Max.
N0. Leads		36			36	
Α	_	_	1.20	_	_	0.047
A1	0.24	_	0.30	0.009	_	0.012
A2	0.60	_	_	0.024		_
D	9.90	10.00	10.10	0.390 (0.394	0.398
D1	5	5.25BSC)	.20	С	
E	7.90	8.00	8.10	0.311 (0.315	0.319
E1	3.75BSC)	0.1	48BS	SC .
е	0.75BSC		2	0.030BSC		SC .
b	0.30	0.35	0.40	0.012 (0.014	0.016

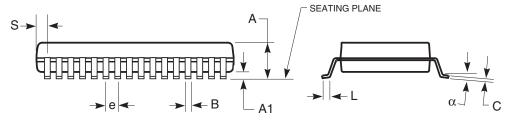
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Plastic TSOP-Type I

Package Code: T (32-pin)





Symbol Min. Max. Min. Max. No. Leads 32 A — 1.20 — 0.047 A1 0.05 0.25 0.002 0.010 B 0.17 0.23 0.007 0.009 C 0.12 0.17 0.005 0.007 D 7.90 8.10 0.311 0.319 E 18.30 18.50 0.720 0.728 H 19.80 20.20 0.780 0.795 e 0.50 BSC 0.020 BSC L 0.40 0.60 0.016 0.024 α 0° 8° 0° 8° S 0.25 REF 0.010 REF		MILLIMETERS			INC	HES
A — 1.20 — 0.047 A1 0.05 0.25 0.002 0.010 B 0.17 0.23 0.007 0.009 C 0.12 0.17 0.005 0.007 D 7.90 8.10 0.311 0.319 E 18.30 18.50 0.720 0.728 H 19.80 20.20 0.780 0.795 e 0.50 BSC 0.020 BSC L 0.40 0.60 0.016 0.024 α 0° 8° 0° 8°	Symbol	Min.	Max.		Min.	Max.
A1 0.05 0.25 0.002 0.010 B 0.17 0.23 0.007 0.009 C 0.12 0.17 0.005 0.007 D 7.90 8.10 0.311 0.319 E 18.30 18.50 0.720 0.728 H 19.80 20.20 0.780 0.795 e 0.50 BSC 0.020 BSC L 0.40 0.60 0.016 0.024 α 0° 8° 0° 8°	No. Leads			32		
B 0.17 0.23 0.007 0.009 C 0.12 0.17 0.005 0.007 D 7.90 8.10 0.311 0.319 E 18.30 18.50 0.720 0.728 H 19.80 20.20 0.780 0.795 e 0.50 BSC 0.020 BSC L 0.40 0.60 0.016 0.024 α 0° 8° 0° 8°	Α	_	1.20		_	0.047
C 0.12 0.17 0.005 0.007 D 7.90 8.10 0.311 0.319 E 18.30 18.50 0.720 0.728 H 19.80 20.20 0.780 0.795 e 0.50 BSC 0.020 BSC L 0.40 0.60 0.016 0.024 α 0° 8° 0° 8°	A1	0.05	0.25		0.002	0.010
D 7.90 8.10 0.311 0.319 E 18.30 18.50 0.720 0.728 H 19.80 20.20 0.780 0.795 e 0.50 BSC 0.020 BSC L 0.40 0.60 0.016 0.024 α 0° 8° 0° 8°	В	0.17	0.23		0.007	0.009
E 18.30 18.50 0.720 0.728 H 19.80 20.20 0.780 0.795 e 0.50 BSC 0.020 BSC L 0.40 0.60 0.016 0.024 α 0° 8° 0° 8°	С	0.12	0.17		0.005	0.007
H 19.80 20.20 0.780 0.795 e 0.50 BSC 0.020 BSC L 0.40 0.60 0.016 0.024 α 0° 8° 0° 8°	D	7.90	8.10		0.311	0.319
e 0.50 BSC 0.020 BSC L 0.40 0.60 0.016 0.024 α 0° 8° 0° 8°	Е	18.30	18.50		0.720	0.728
L 0.40 0.60 0.016 0.024 α 0° 8° 0° 8°	Н	19.80	20.20		0.780	0.795
α 0° 8° 0° 8°	е	0.50 BSC			0.020	BSC
	L	0.40	0.60		0.016	0.024
S 0.25 REF 0.010 REF	α	0°	8°		0°	8°
·	S	0.25 REF			0.010	REF

Notes:

- 1. Controlling dimension: millimeters, unless otherwise specified.
- 2. BSC = Basic lead spacing between centers.
- Dimensions D and E do not include mold flash protrusions and should be measured from the bottom of the package.
- Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.

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